

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	18mΩ@10V	35A
	22mΩ@4.5V	



合肥矽普半导体

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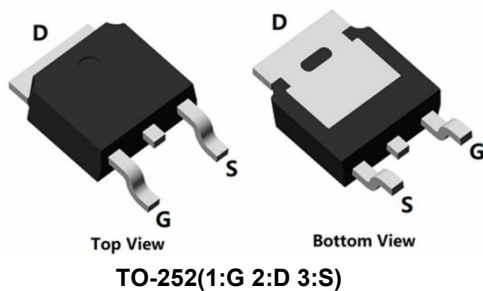
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

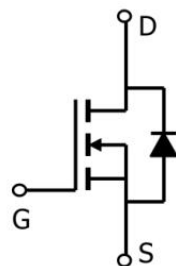
Applications

- Power switching application
- Battery management
- Uninterruptible power supply

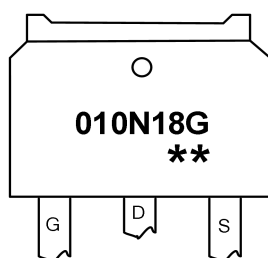
Package



Circuit diagram



Marking



010N18G : Product code
****** : Week code

Order Information

Device	Package	Unit/Tube
SP010N18GTH	TO-252	2500

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	35	A
Continuous Drain Current (Tc=100°C)	I_D	23	A
Pulsed Drain Current	I_{DM}	140	A
Single Pulse Avalanche Energy ¹	E_{AS}	81	mJ
Power Dissipation (Tc=25°C)	P_D	55	W
Power Dissipation (Tc=100°C)	P_D	22	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	2.27	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

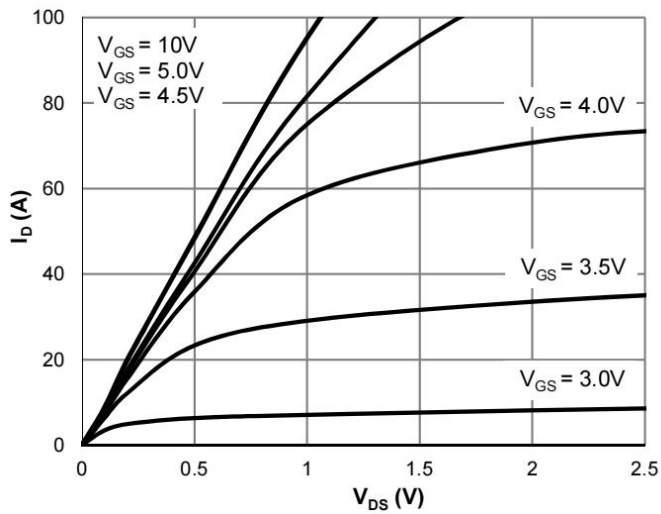
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	100	-	-	V
Drain Cut-Off Current	IDSS	VDS=80V , VGS=0V , TJ=25℃	-	-	1	μA
Gate Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID=250uA	1.3	1.7	2.3	V
Drain-Source ON Resistance	RDS(ON)	VGS=10V , ID=20A	-	18	23	mΩ
		VGS=4.5V , ID=10A	-	22	29	
Gate Resistance	RG	VDS=50V , VGS=0V , f=1MHz	-	1.3	-	Ω
Dynamic Characteristics						
Input Capacitance	Ciss	VDS=50V , VGS=0V , f=1MHz	-	880	-	pF
Output Capacitance	Coss		-	258	-	
Reverse Transfer Capacitance	Crss		-	12	-	
Total Gate Charge	Qg	VDS=50V , VGS=10V , ID=20A	-	10	-	nC
Gate-Source Charge	Qgs		-	3.6	-	
Gate-Drain Charge	Qgd		-	1.9	-	
Gate Plateau Voltage	Vplateau		-	3.2	-	V
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=50V, VGS=10V , RG=2.2Ω , ID=20A	-	36	-	nS
Rise Time	tr		-	11.4	-	
Turn-Off Delay Time	td(off)		-	48	-	
Fall Time	tf		-	16	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	VSD	IS=1A , VGS=0V , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	35	A
Reverse Recovery Time	Trr	IS=20A , di/dt=100A/us , TJ=25℃	-	35	-	nS
Reverse Recovery Charge	Qrr		-	33	-	nC

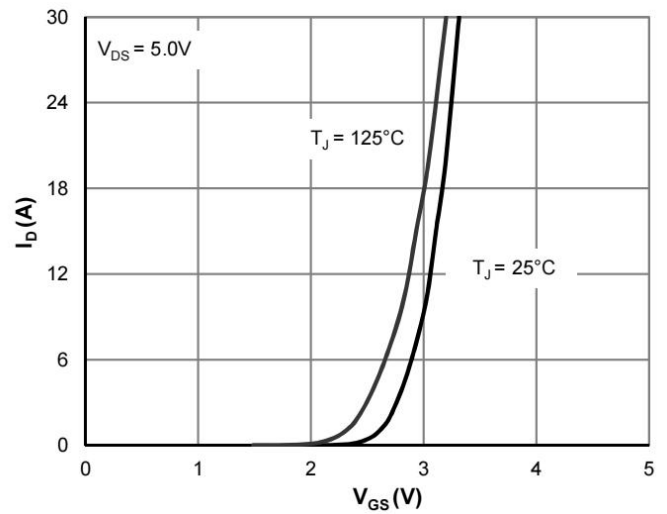
Note:

- The EAS test condition is $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

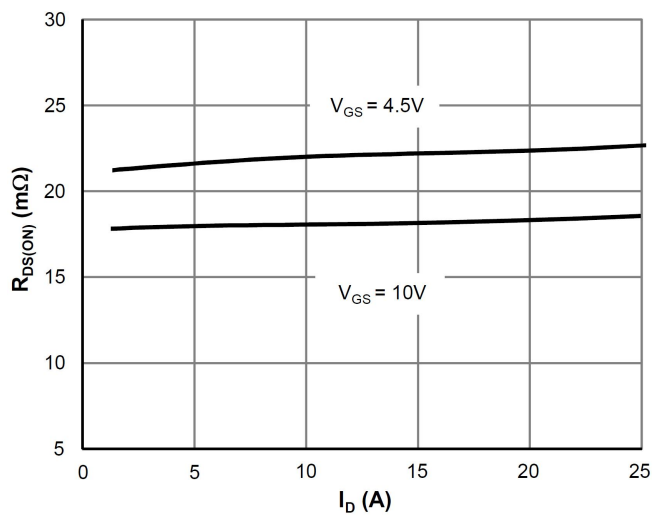
Typical Characteristics



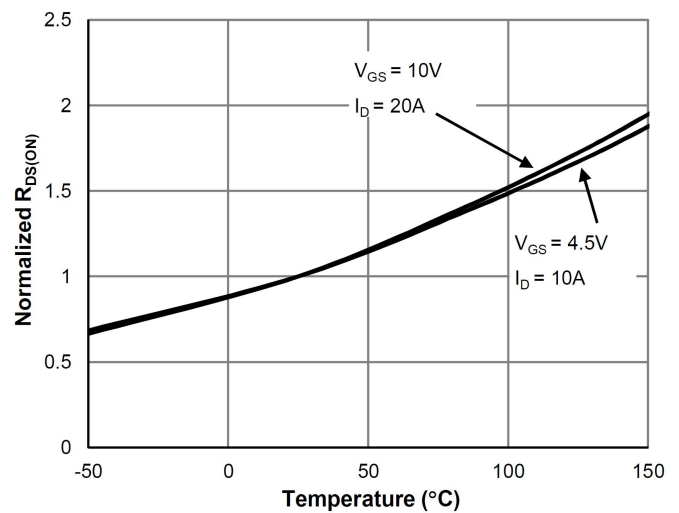
Typical Output Characteristics



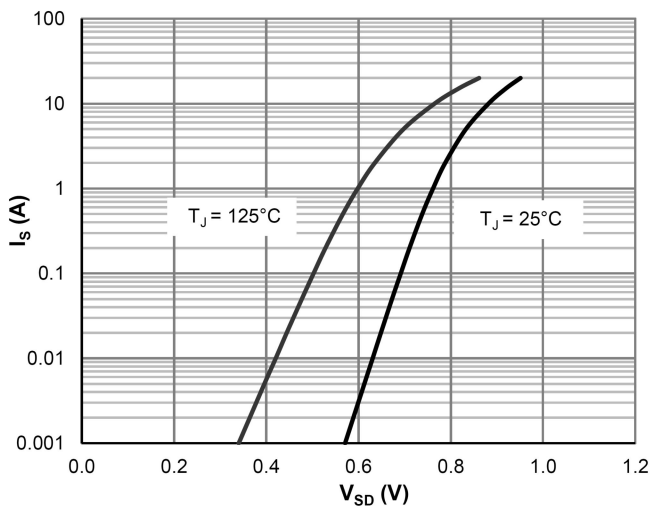
Transfer Characteristics



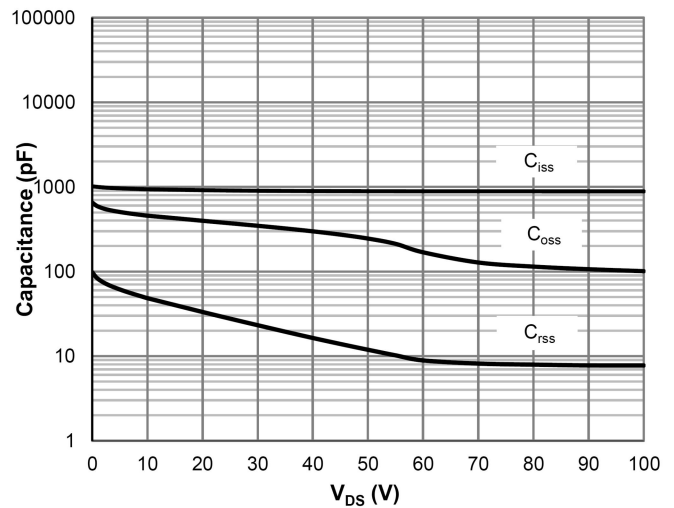
On-Resistance vs. Drain Current



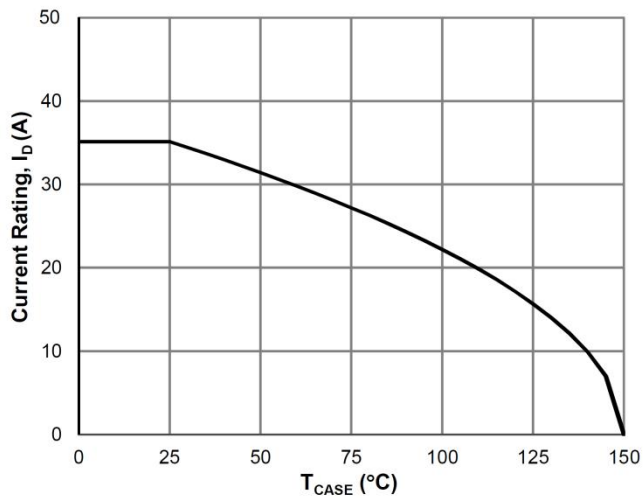
On-Resistance vs. Junction Temperature



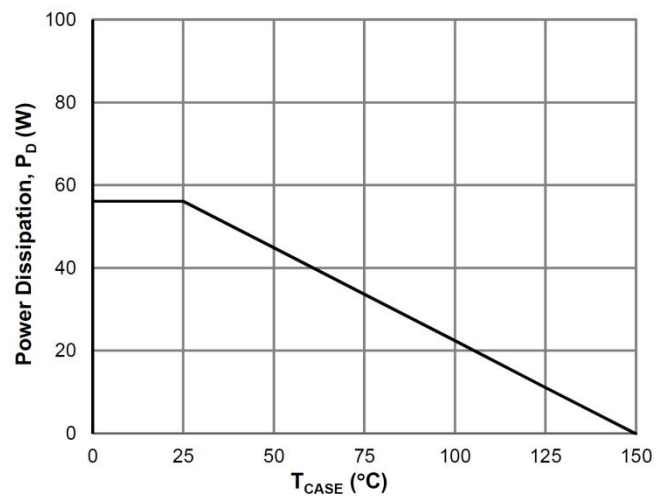
Body-Diode Characteristics



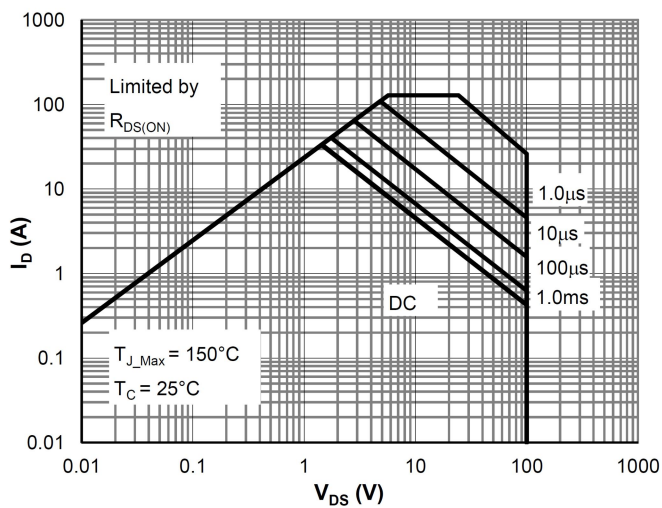
Capacitance Characteristics



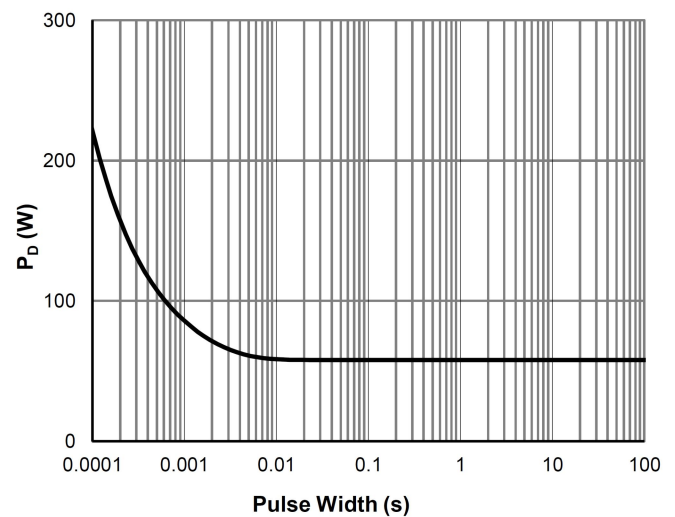
Current De-rating



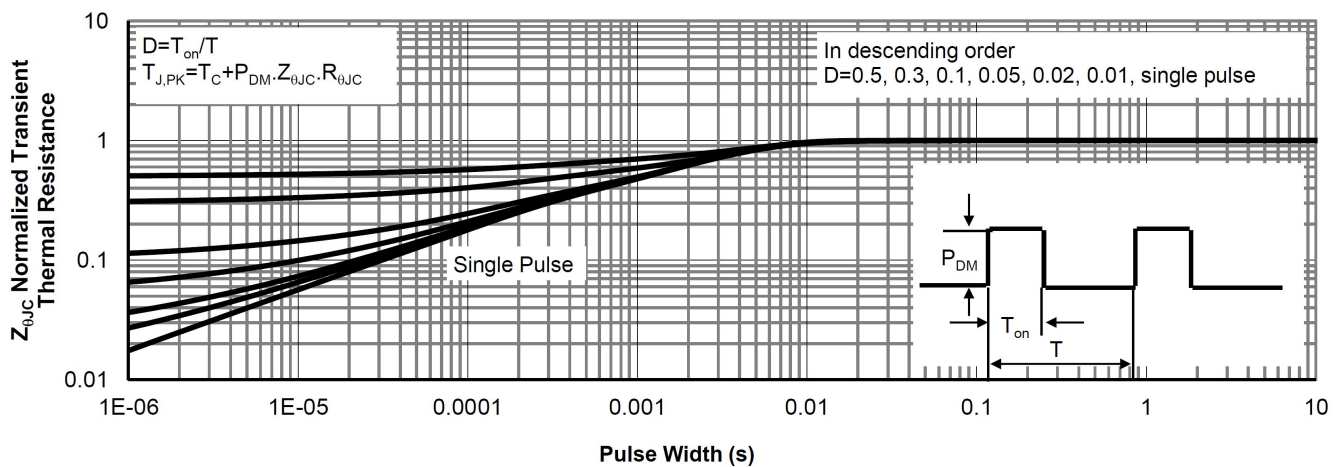
Power De-rating



Maximum Safe Operating Area



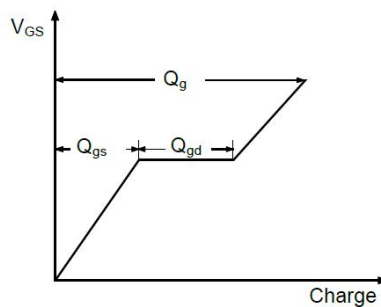
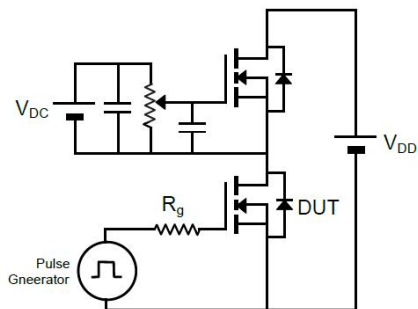
Single Pulse Power Rating, Junction-to-Case



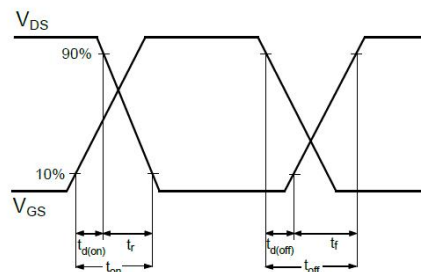
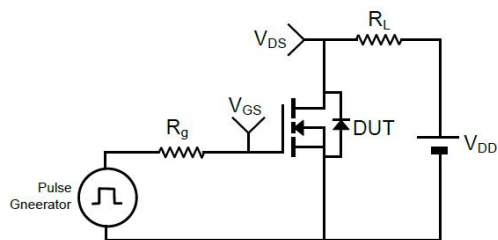
Normalized Maximum Transient Thermal Impedance

Test Circuit

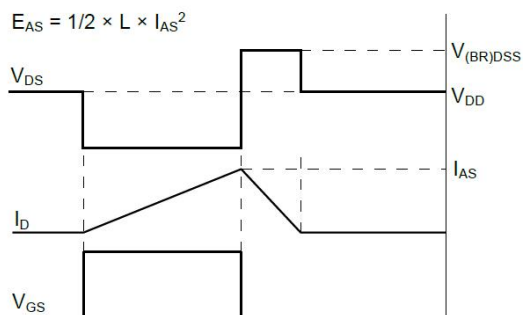
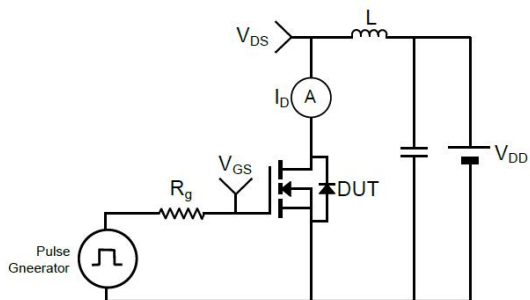
Gate Charge



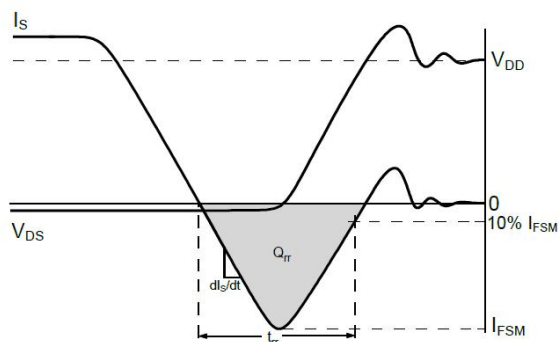
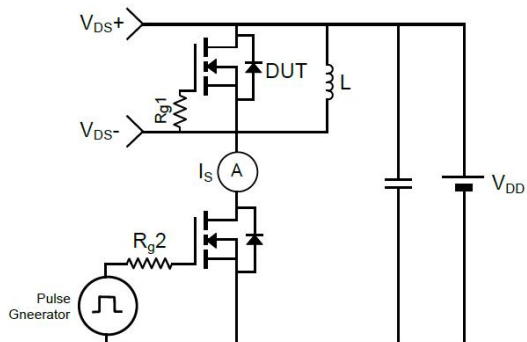
Resistive Load Switching Time

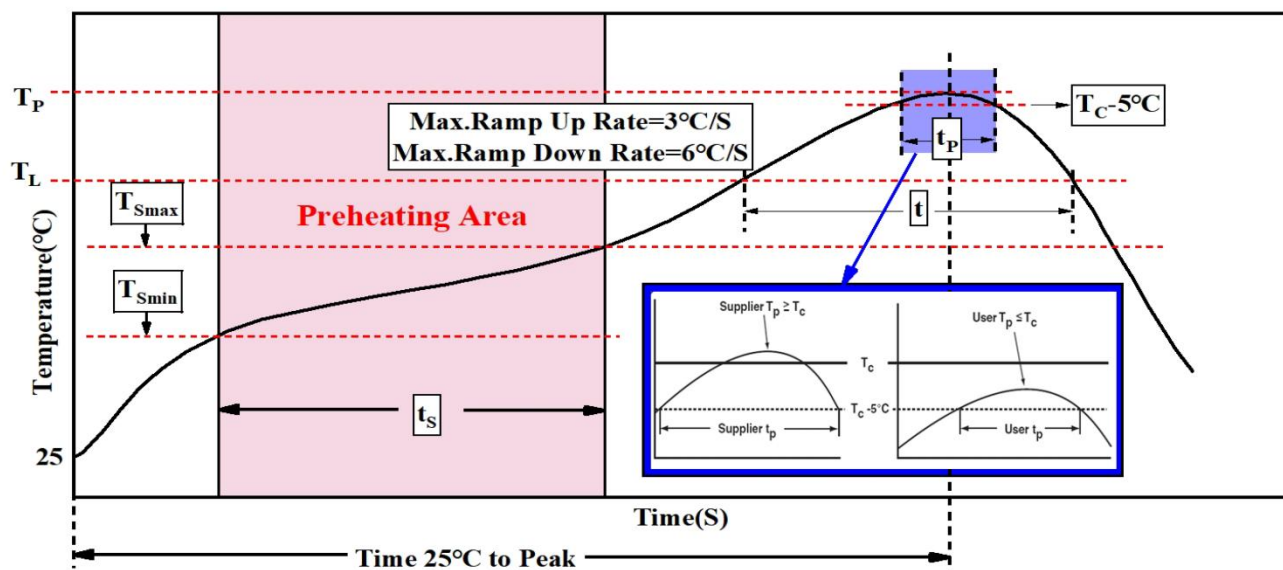


Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering


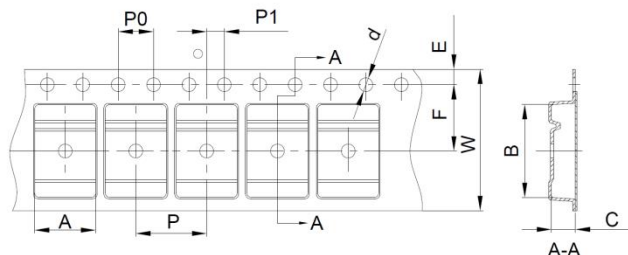
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{Smin})	100°C	150°C
Temperature max (T_{Smax})	150°C	200°C
Time (T_{Smin} to T_{Smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{Smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217°C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T_P)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_C)	20** seconds	30** seconds
Average ramp-down rate (T_P to T_{Smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_P) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_P) is defined as a supplier minimum and a user maximum		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

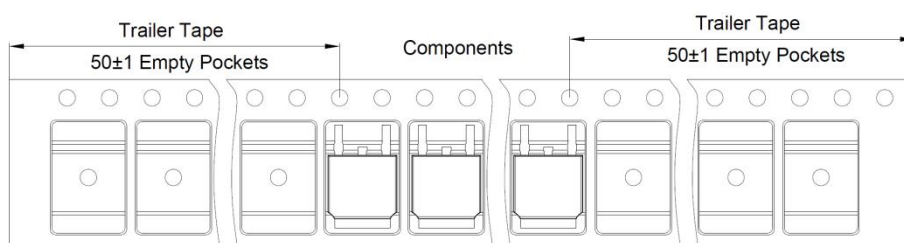
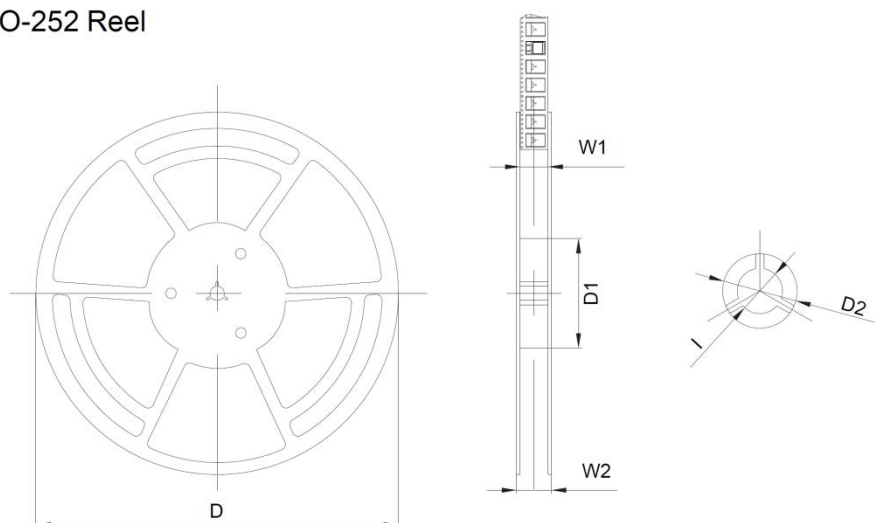
Table 2. Pb-free Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

TO-252 Embossed Carrier Tape

Packaging Description:

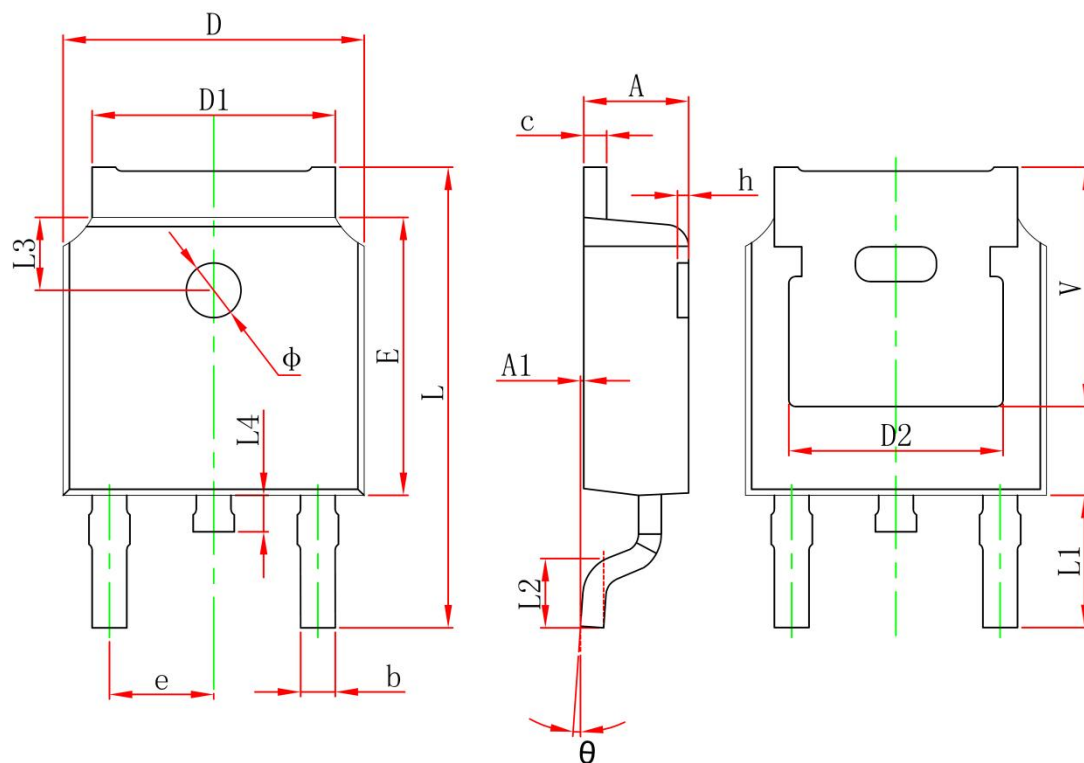
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Hear Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2500 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Φ1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer

TO-252 Reel


Dimensions are in millimeter						
Reel	D	D1	D2	W1	W2	I
13" Dia	330.00	100.00	Φ21.00	16.40	21.40	Φ13.00

Reel	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
2500 pcs	13 inch	5000 pcs	360×360×65	25000 pcs	378×358×382

TO-252 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	